

1A 40V(0.82mm)

Chip Information

Chip Size	0.82 x 0.82mm
Pad Size	0.68 x 0.68mm
Chip Quantity	16276 pcs/wafer
Scribe Line Width	60um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al-Ni-Au (For Solder)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	1	A	
Peak Forward Surge Current	IFSM	40	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition	
Maximum Forward Voltage	VF1	0.500		0.460	V	IF=1A Ta=25degC	
	VF2				V		
	VF3				V		
	VF4				V		
	VF5				V		
Maximum DC Reverse Current	IR1	0.2	0.1	0.008	mA	VR=42V Ta=25degC VR=40V Ta=100deg	
	IR2				1		mA
	IR3				mA		
	IR4				mA		
Reverse Breakdown Voltage	BV	42	44	51	V	IR=0.08mA	
Junction Capacitance	Cj				pF		
Reverse Recovery Time	trr				nS		

Ordering Information

Chip Type	Chip Thickness	Back metal
XHT512	250 +/- 20um	Ti-Ni-Au (For Solder)

Note:
Designed For 1N5818,1N5819,B140,SR104